

TO-126 Plastic-Encapsulate Transistors

BD234/236/238 TRANSISTOR (PNP)

FEATURES

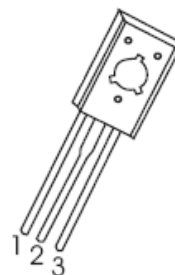
- Power Dissipation

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	BD234	-45
		BD236	-60
		BD238	-100
V _{CEO}	Collector-Emitter Voltage	BD234	-45
		BD236	-60
		BD238	-80
V _{EBO}	Emitter-Base Voltage	BD234	-5
		BD236	-5
		BD238	-5
I _C	Collector Current –Continuous	-2	A
P _C	Collector Power Dissipation	1.25	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

TO-126

1. EMITTER
2. COLLECTOR
3. BASE



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	BD234 BD236 BD238	V _{(BR)CBO}	I _C =-1mA, I _E =0	-45 -60 -100	V
Collector-emitter breakdown voltage	BD234 BD236 BD238	V _{(BR)CEO}	I _C =-100mA, I _B =0	-45 -60 -80	V
Emitter-base breakdown voltage		V _{(BR)EBO}	I _E =-1mA, I _C =0	-5	V
Collector cut-off current	BD234 BD236 BD238	I _{CBO}	V _{CB} =-45V, I _E =0 V _{CB} =-60V, I _E =0 V _{CB} =-100V, I _E =0	-100	μA
Emitter cut-off current		I _{EBO}	V _{EB} =-5V, I _C =0	-1	mA
DC current gain		h _{FE(1)}	V _{CE} =-2V, I _C =-150mA	40	
		h _{FE(2)}	V _{CE} =-2V, I _C =-1A	25	
Collector-emitter saturation voltage		V _{CE(sat)}	I _C =-1A, I _B =-100mA	-0.6	V
Transition frequency		f _T	V _{CE} =-10V, I _C =-250mA, f = 10MHz	3	MHz